

**METHOD FOR THE PRODUCTION OF A MEMORY CELL, MEMORY
CELL AND MEMORY CELL ARRANGEMENT**

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Abstract

The invention relates to a method for the production of a memory cell, a memory cell and a memory cell arrangement. According to the inventive method for the production of a memory cell, a first electrically conductive area is formed in 10 and/or on a substrate. A second electrically conductive area is also formed at a given distance from the first electrically conductive area such that a cavity is formed between the first and second electrically conductive areas. The first and second electrically conductive areas are configured in such a way that when a first voltage is applied to the electrically conductive areas, a structure is formed from 15 material from at least one of said electrically conductive areas, at least partially bridging over the distance between the electrically conductive areas. When a second voltage is applied to the conductive areas, the material of the structure at least partially bridging over the distance between the electrically conductive areas recedes.